Session Program

27 September 2026 to 2 October 2026

GADEST 2026

Poster Session - 1

GADEST 2026 - San Servolo Island, Venice (Italy)

Monday 28 September

19:00

Poster Session - 1

Poster Session | **Location:** Grecale Hall E

Radiation-induced defect reactions in Silicon Junction Barrier Schottky Diodes upon irradiation with alpha particles in different regimes

Speaker
Dr Vladimir Markevich

Electrical Properties of Dislocation-Related Defects in Ge/Si Virtual Substrates

Speaker
Henriette Tetzner

Search for stable atomic configurations in SiGe, SiSn, and GeSn alloys using DFT and optimization algorithms

Speaker
Koji Sueoka

Superacid-based diagnosis of damage in high-carrier-lifetime crystalline silicon

Speaker
Sophie Pain

Surface passivation of silicon by ZnO/Al2O3 stacks with controlled SiOx interlayers

Speaker
John Murphy

Epi stacking fault defects in highly doped phosphorus 300 mm crystals

Speaker
Matteo Pannocchia

Controlled Copper Precipitation for Rapid Point Defect Characterization in Near-Perfect Czochralski Silicon

Speaker
Shuai Yuan

Evaluation of impurity effects in magic-angle twisted bilayer graphene by machine learning interatomic potentials

Speaker
Ignazio Vacante

Doping Engineering of Double-SOI Structures for Two-Channel Tunneling Transistors

Speaker
Dr Shengqiang Zhou

On the formation of local molten regions on Si surfaces by pulsed laser annealing at the melting threshold

Speaker
Dr SEBASTIEN KERDILES

Experimental observation and analysis of gliding I3 basal stacking faults in hexagonal germanium

Speaker
Mette Schouten

Mechanism of slip line propagation in advanced 300mm silicon substrates

Speaker
Dr Alexandra Abbadie

Pulsed Laser Melting for TOPCon technology: new routes to higher efficiency

Speaker
Francesco Sgarbossa

Elimination of slip lines induced by the pins in rapid thermal processing for Czochralski silicon wafers

Speaker
Yilun Wang

Electric Field Distribution in Black Silicon Needles Under Reverse Bias: A TCAD Simulation Study

Speaker
Oskari Leiviskä

Electrically detected magnetic resonance of telecom-wavelength G and C centers in silicon

Speaker
Alessandro Puddu

Impact of Substrate Carbon Impurities on MOSFET Breakdown Voltage via Enhanced Phosphorus Out-Diffusion in n/n$^+$ Epitaxial Wafers

Speaker
Jinge Wang

On the gettering properties of isovalent tin and lead impurities in n-type Czochralski silicon

Speaker
Dr Mykola Kras'ko

Progress in understanding optically detected magnetic resonance (ODMR) spectra of ASi-Sii-defects

Speaker
Kevin Lauer

Theoretical study on the stability of Sn atom in Ge thin film grown on GaSb substrates

Speaker
Dr Koji Ozawa

Admittance spectroscopy of organic-silicon heterojunction structures fabricated with ultrasound assistance

Speaker
Prof. Oleg Olikh

Electrical and Optical Properties of Defect-Enhanced SiGe Heterostructures

Speaker
kaynat alvi

Infrared properties of a perfectly compensated germanium doped with shallow donors and acceptors below the Mott transition

Speaker
Dr Sergey Pavlov

Ge-on-Si Substrates with Porous Silicon buffer as Compliant Layer

Speaker
Dr Charlotte Weiss

Elusive point radiation defects in proton-irradiated silicon and germanium

Speaker
Dr Nikolay Arutyunov

Optically detected spin properties of the telecom L-band C center in silicon

Speaker
Shuyu Wen

Engineering Nanostructured Electrodes on Screen-Printed Carbon for Real-Time Monitoring of Nitrogen-Based Water Pollutants

Speaker
Dr Roberta Farina

Experimental and simulated investigation of nitrogen shallow donors in Czochralski silicon wafers doped with nitrogen

Speaker
Dr Dawid Kot

Comparative study of void defect annihilation in Si (100) and Si (110) wafers during high-temperature rapid thermal processing

Speaker
Mr Takuya Kusunoki

DFT Analysis of Gettering in Si Wafers for CMOS Image Sensors

Speaker
Dr Iori Takeda

Unlocking high throughput material discovery on defective interfaces

Speaker
Dr Artem Musiienko

Origin of optically active Er3+ sites in Silicon on Insulator-based photonic waveguides

Speaker
Yanan Xu

Structure loss during the Czochralski silicon process: causes, remedies and ML aid

22:00

Speaker

Marisa Di Sabatino